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(54) **METHOD FOR FORMING INTERCONNECT STRUCTURE**

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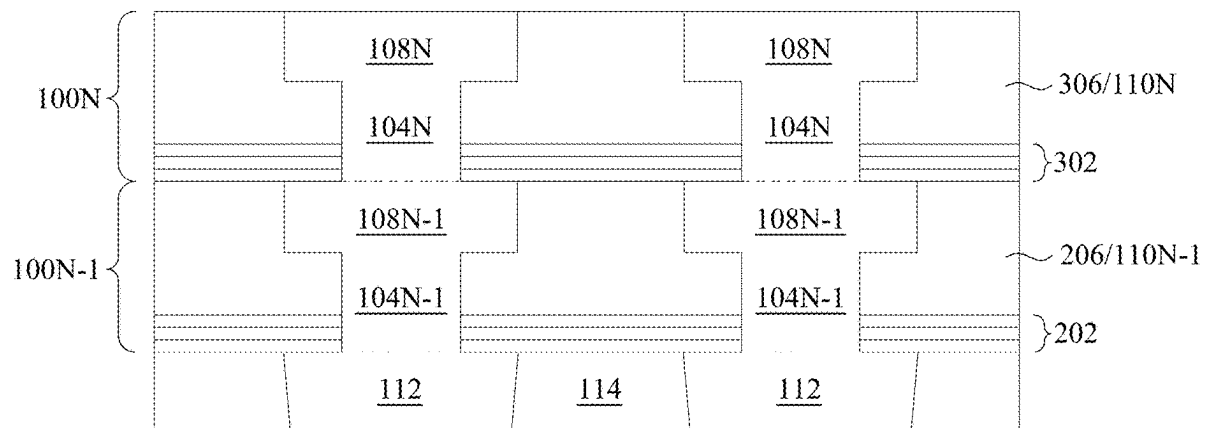
**Related U.S. Application Data**

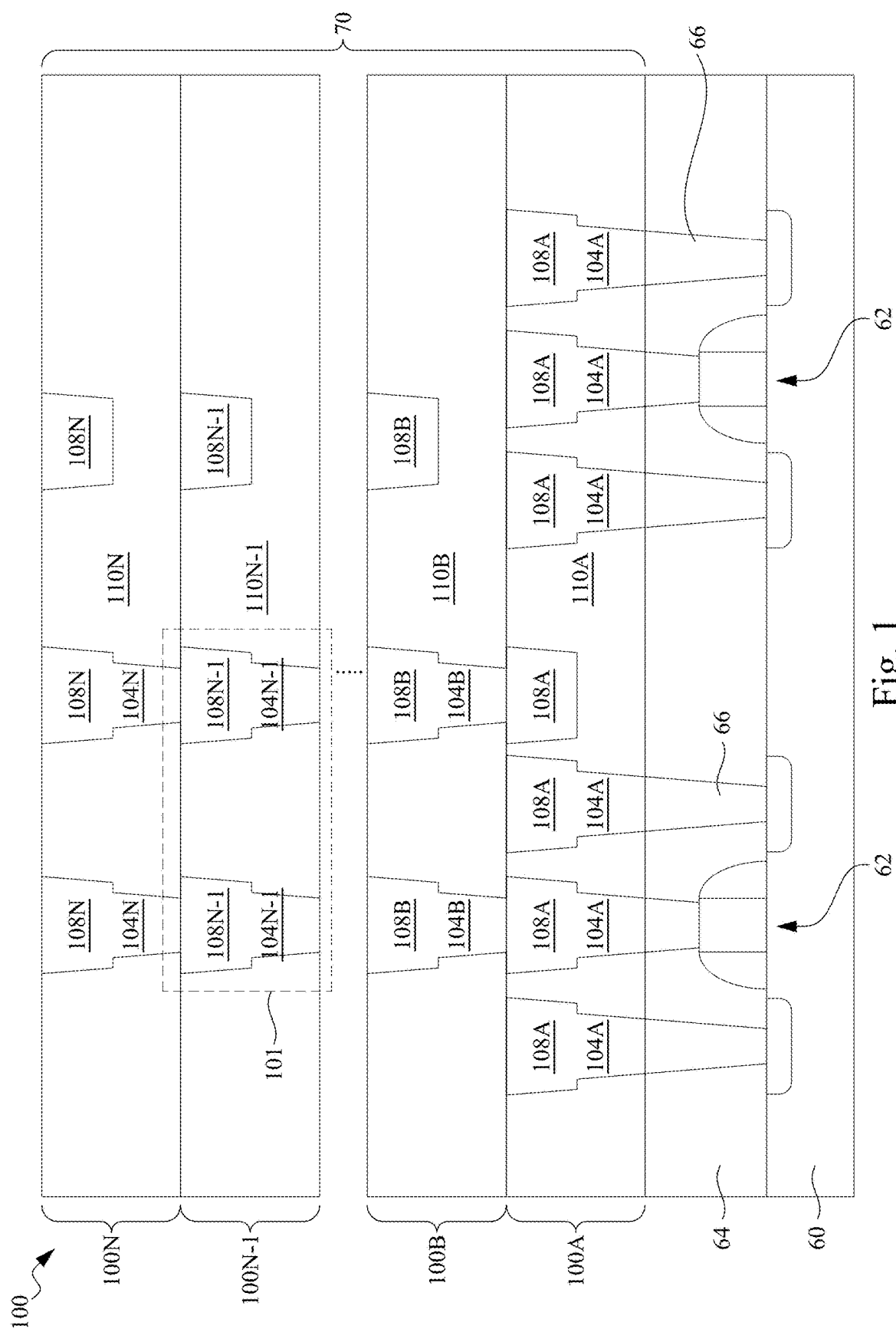
(63) Continuation of application No. 18/498,851, filed on Oct. 31, 2023, now Pat. No. 12,308,283, which is a continuation of application No. 17/399,262, filed on Aug. 11, 2021, now Pat. No. 11,842,922.

(57) **ABSTRACT**

A method includes depositing a first dielectric layer over a first conductive feature, depositing a first mask layer over the first dielectric layer, and depositing a second mask layer over the first mask layer. A first opening is patterned in the first mask layer and the second mask layer, the first opening having a first width. A second opening is patterned in a bottom surface of the first opening, the second opening extending into the first dielectric layer, the second opening having a second width. The second width is less than the first width. The first opening is extended into the first dielectric layer and the second opening is extended through the first dielectric layer to expose a top surface of the first conductive feature.

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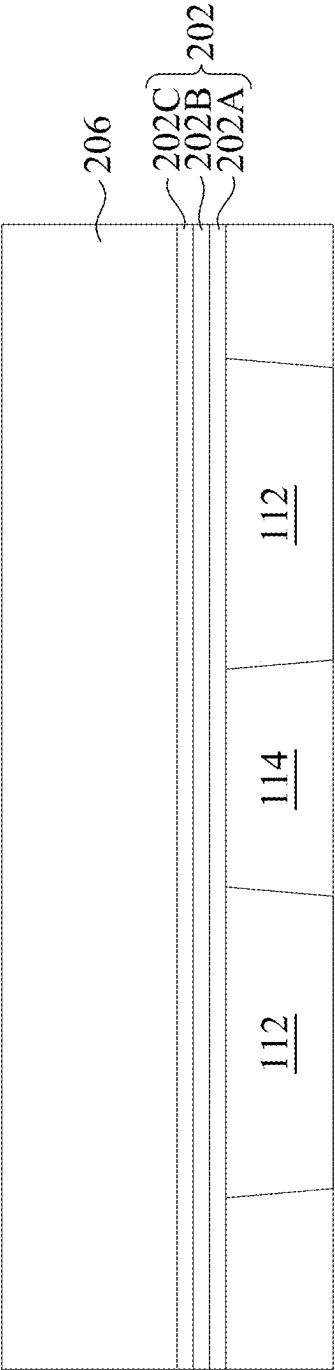


Fig. 2

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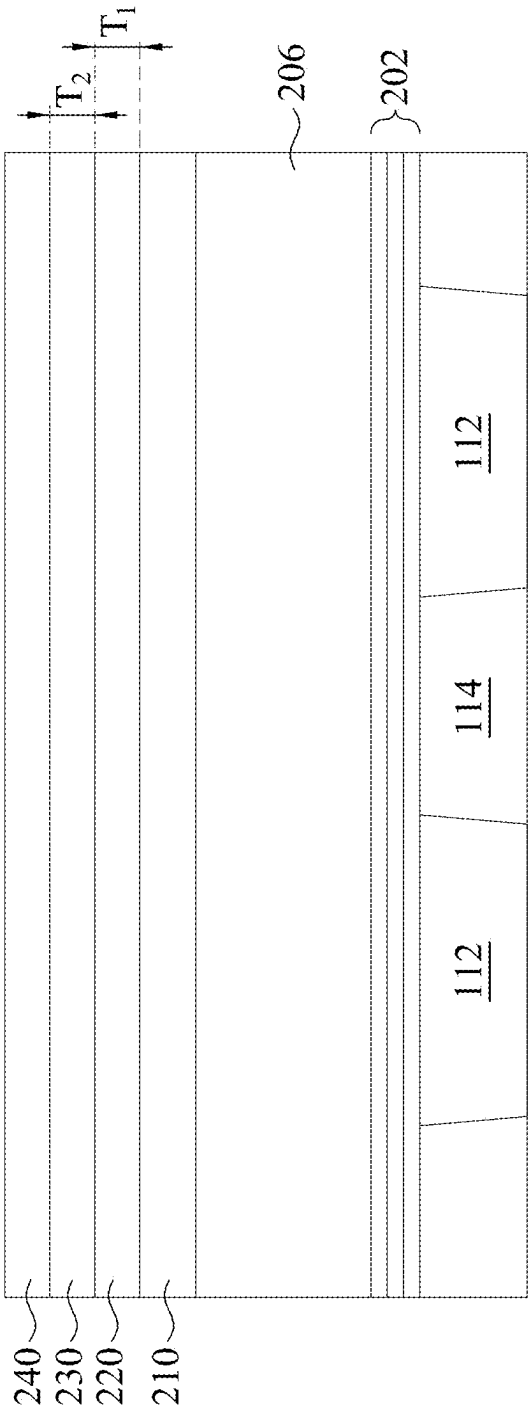


Fig. 3

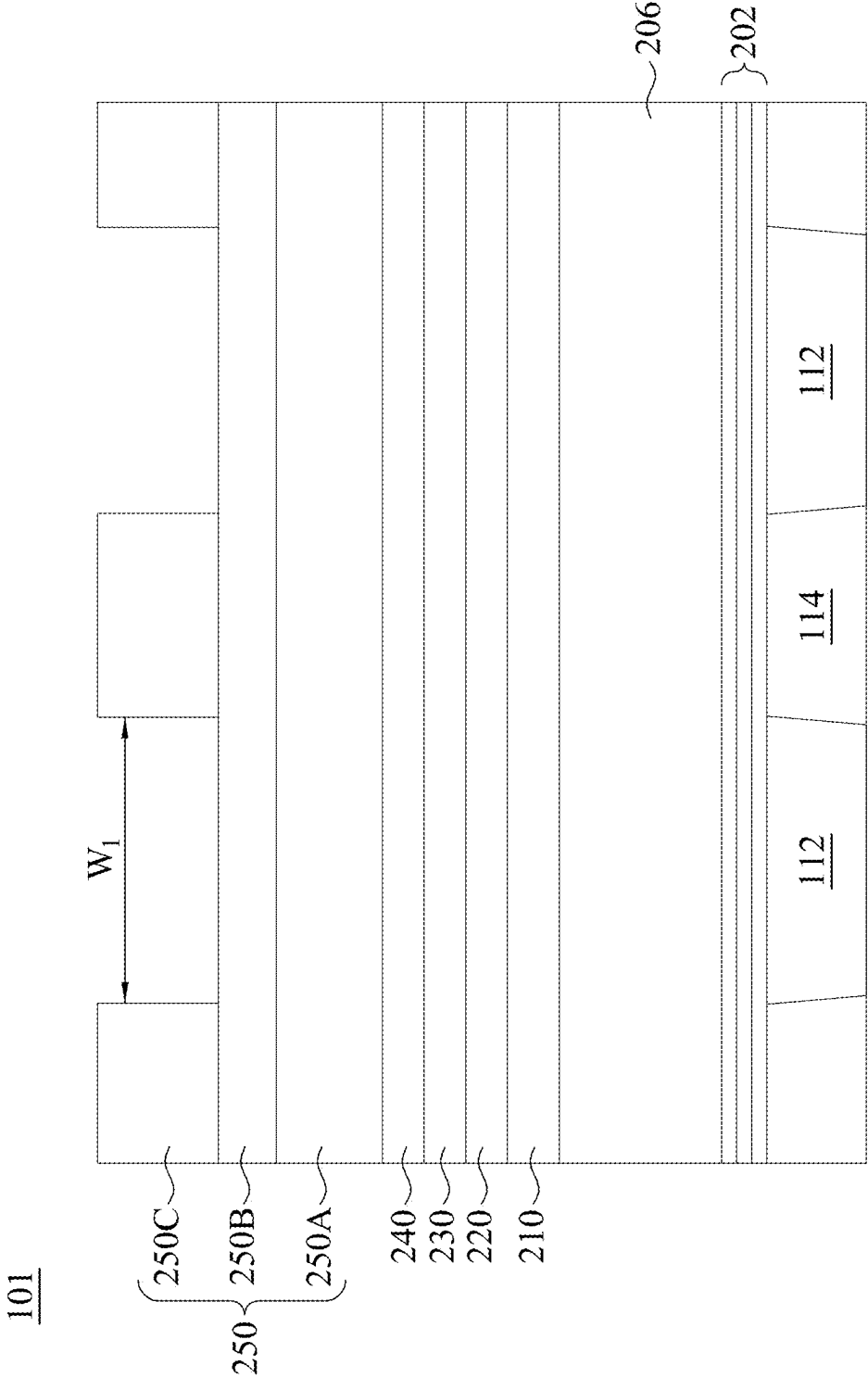


Fig. 4

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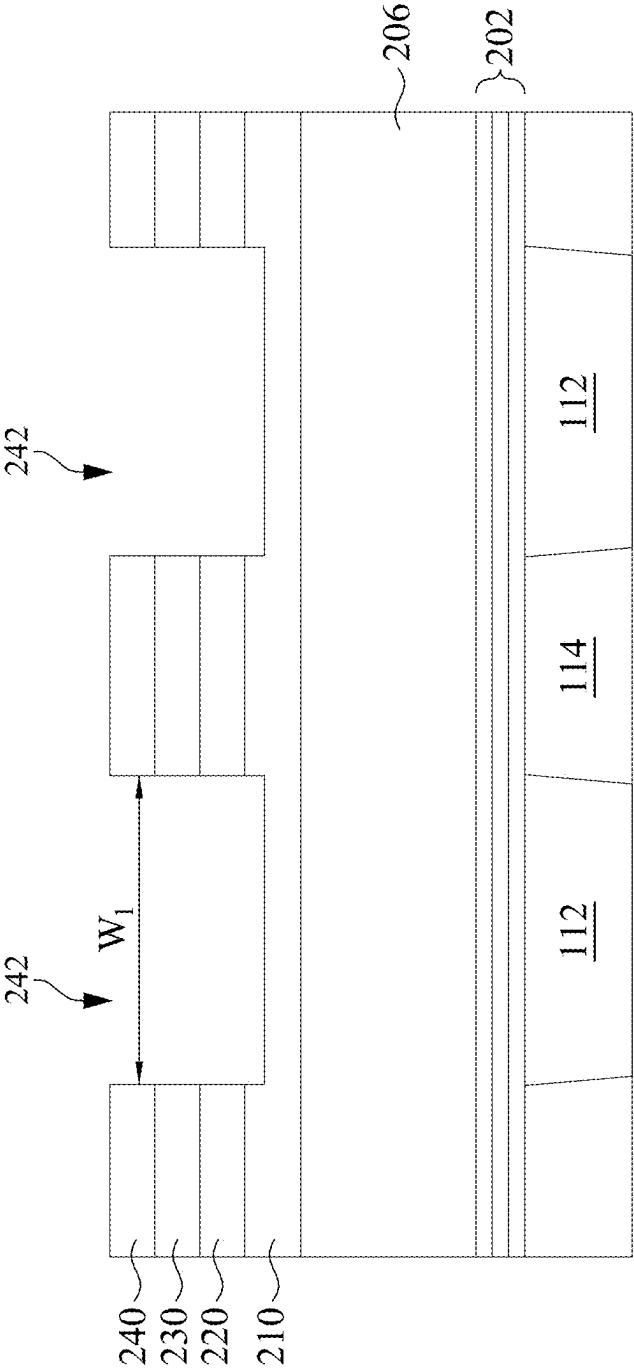


Fig. 5

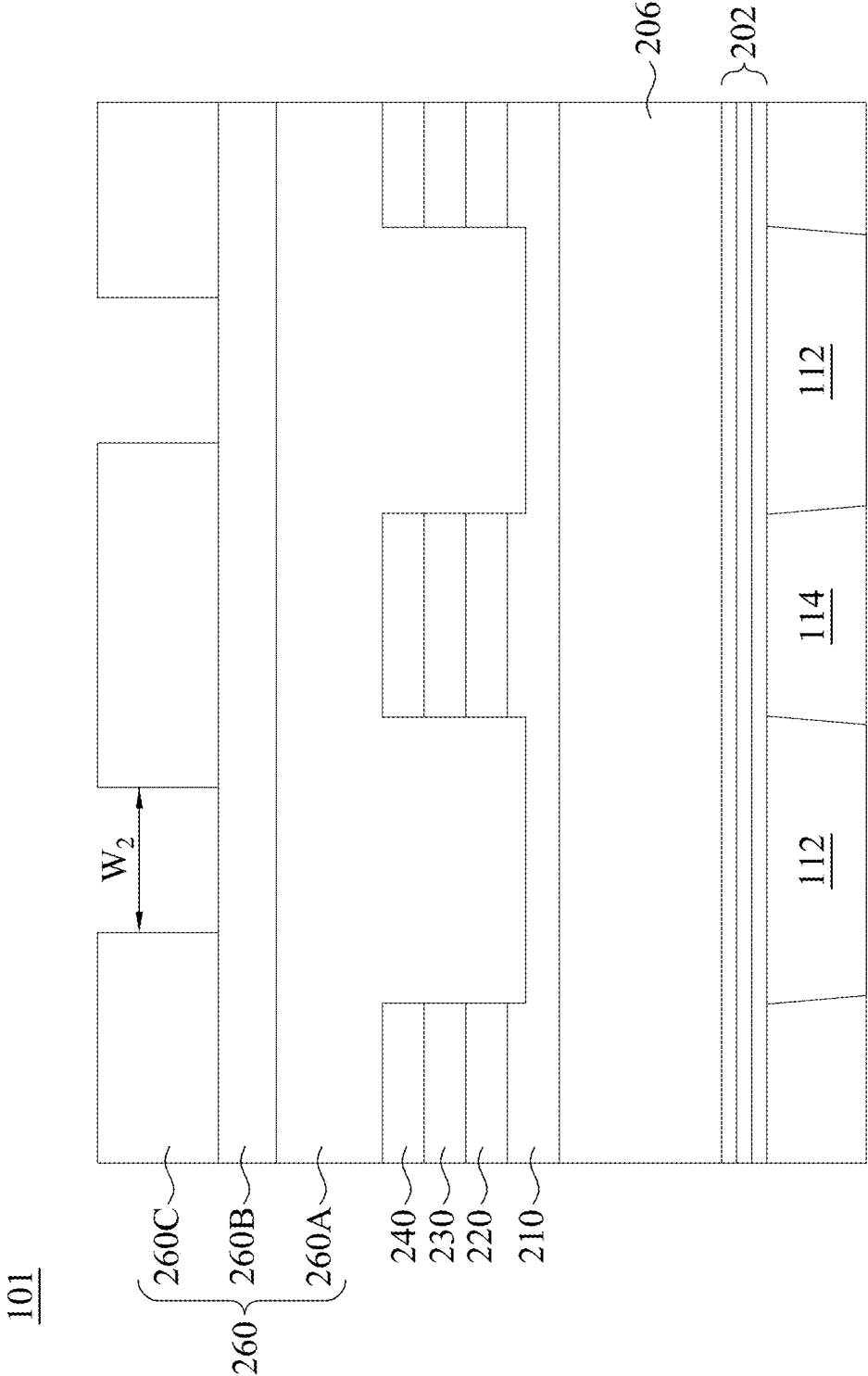


Fig. 6

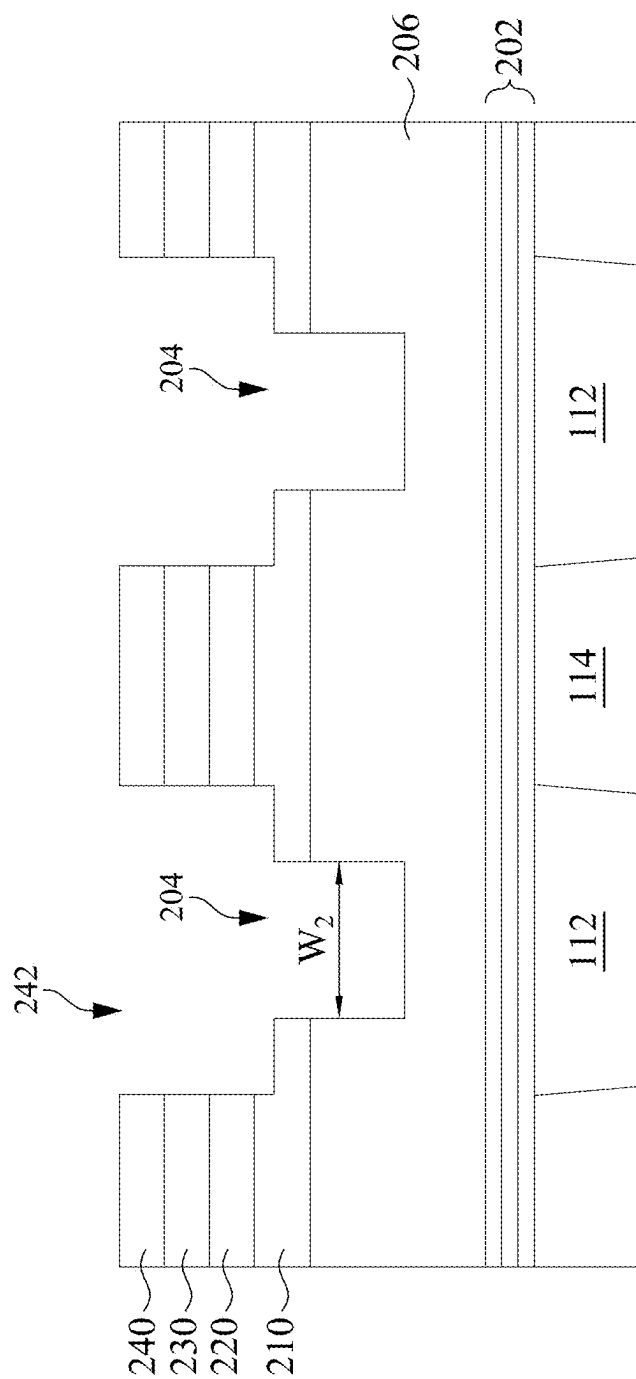


Fig. 7



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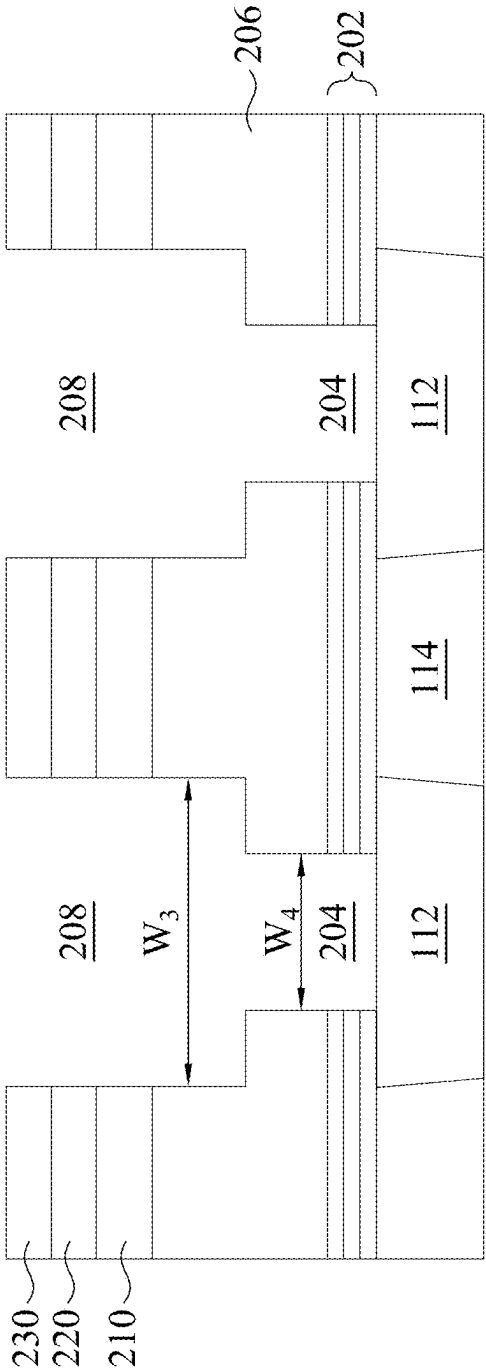


Fig. 8

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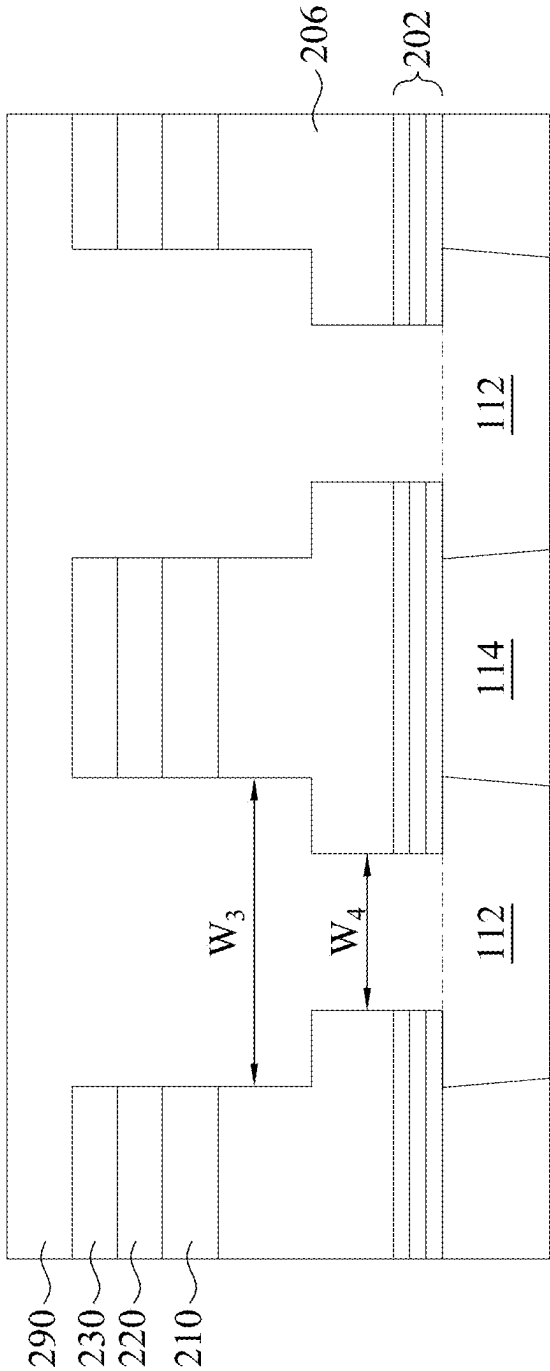


Fig. 9

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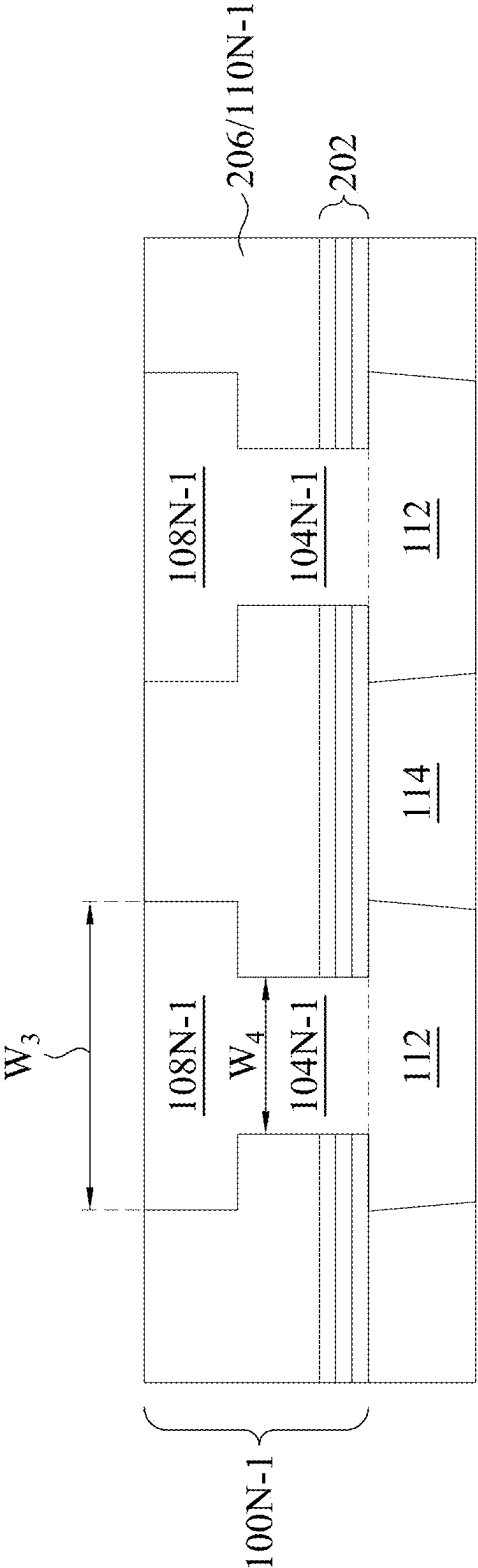
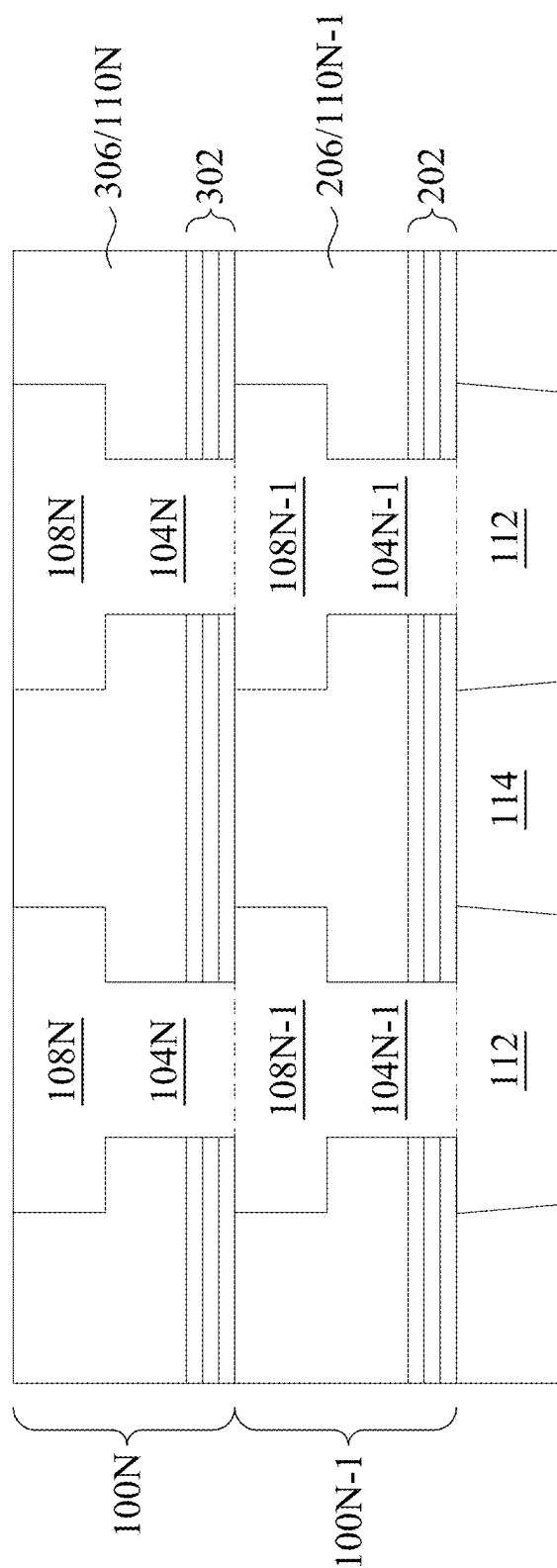


Fig. 10

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Fi. 11

## METHOD FOR FORMING INTERCONNECT STRUCTURE

### PRIORITY CLAIM AND CROSS-REFERENCE

[0001] This application is a continuation of U.S. patent application Ser. No. 18/498,851, filed on Oct. 31, 2023, entitled “Method for Forming Interconnect Structure,” which is a continuation of U.S. patent application Ser. No. 17/399,262, filed on Aug. 11, 2021, entitled “Method for Forming Interconnect Structure,” now U.S. Pat. No. 11,842,922, issued on Dec. 12, 2023, which applications are hereby incorporated herein by reference.

### BACKGROUND

[0002] The semiconductor integrated circuit (IC) industry has experienced exponential growth. Technological advances in IC materials and design have produced generations of ICs where each generation has smaller and more complex circuits than the previous generation. In the course of IC evolution, functional density (e.g., the number of interconnected devices per chip area) has generally increased while geometry size (e.g., the smallest component (or line) that can be created using a fabrication process) has decreased. This scaling down process generally provides benefits by increasing production efficiency and lowering associated costs.

[0003] Accompanying the scaling down of devices, manufacturers have begun using new and different materials and/or combination of materials to facilitate the scaling down of devices. Scaling down, alone and in combination with new and different materials, has also led to challenges that may not have been presented by previous generations at larger geometries.

### BRIEF DESCRIPTION OF THE DRAWINGS

[0004] Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It is noted that, in accordance with the standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

[0005] FIG. 1 illustrates a cross-sectional view of a semiconductor substrate and multilevel interconnect structures of an integrated circuit, in accordance with some embodiments.

[0006] FIGS. 2 through 10 illustrate cross-sectional views of a semiconductor device at various intermediate stages of fabrication, in accordance with some embodiments.

[0007] FIG. 11 illustrates a cross-sectional view of a semiconductor device at an intermediate stage of fabrication, in accordance with some embodiments.

### DETAILED DESCRIPTION

[0008] The following disclosure provides many different embodiments, or examples, for implementing different features of the invention. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be

formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed.

[0009] Further, spatially relative terms, such as “beneath,” “below,” “lower,” “above,” “upper” and the like, may be used herein for ease of description to describe one element or feature’s relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. The apparatus may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

[0010] The present disclosure includes, for example, methods of forming masks for the patterning of interconnect openings (including trenches and via openings) with a dual damascene process. For example, a mask may comprise a titanium-containing mask layer over a tungsten-containing mask layer. The titanium-containing mask layer may provide high etching selectivity with underlying dielectric materials for forming interconnect openings in the dielectric materials with a dual damascene process. The tungsten-containing mask layer may, by nature of having a strong physical modulus, reduce distortion of the interconnect openings. Further, inclusion of the tungsten-containing mask layer in the multi-layer mask helps reduce the quantity of non-volatile etching byproducts during the patterning of the interconnect openings, thereby reducing under-etching.

[0011] FIG. 1 illustrates a cross-sectional view of a semiconductor device 100, in accordance with some embodiments. The semiconductor device 100 includes a semiconductor substrate 60 comprising electronic devices, and an interconnect structure 70 over the semiconductor substrate 60 that interconnects the electronic devices to form an integrated circuit. FIG. 1 is a simplified view of the semiconductor device 100, and some features of the semiconductor device 100 (discussed below) are omitted for clarity of illustration.

[0012] The semiconductor substrate 60 may comprise a bulk semiconductor substrate or a silicon-on-insulator (SOI) substrate. An SOI substrate includes an insulator layer below a thin semiconductor layer that is the active layer of the SOI substrate. The semiconductor of the active layer and the bulk semiconductor generally comprise the crystalline semiconductor material silicon, but may include one or more other semiconductor materials such as germanium, silicon-germanium alloys, compound semiconductors (e.g., GaAs, AlAs, InAs, GaN, AlN, and the like), or their alloys (e.g., Ga<sub>x</sub>Al<sub>1-x</sub>As, Ga<sub>x</sub>Al<sub>1-x</sub>N, In<sub>x</sub>Ga<sub>1-x</sub>As and the like), oxide semiconductors (e.g., ZnO, SnO<sub>2</sub>, TiO<sub>2</sub>, Ga<sub>2</sub>O<sub>3</sub>, and the like) or combinations thereof. The semiconductor materials may be doped or undoped. Other substrates that may be used include multi-layered substrates, gradient substrates, or hybrid orientation substrates.

[0013] Devices 62 are formed at the active surface of the semiconductor substrate 60. The devices 62 may be active devices, passive devices, or a combination thereof. For

example, the devices **62** may be transistors, diodes, capacitors, resistors, or the like, formed by any suitable formation method.

**[0014]** One or more inter-layer dielectric (ILD) layer(s) **64** are formed on the semiconductor substrate **60**, and electrically conductive features, such as contacts **66** (also referred to as contact plugs), are formed physically and electrically coupled to the devices **62**. The ILD layer(s) **64** may be formed of any suitable dielectric material, for example, an oxide such as silicon oxide, phosphosilicate glass (PSG), borosilicate glass (BSG), boron-doped phosphosilicate glass (BPSG), or the like; a nitride such as silicon nitride; or the like. The ILD layer(s) **64** may be formed by any suitable deposition process, such as spin coating, physical vapor deposition (PVD), chemical vapor deposition (CVD), the like, or a combination thereof. The contacts **66** may be formed by any suitable process, such as deposition, damascene (e.g., single damascene, dual damascene, etc.), the like, or combinations thereof.

**[0015]** The interconnect structure **70** includes multiple interconnect levels **100A-100N**, which are stacked vertically above the contacts **66** and the ILD layer(s) **64**. The interconnect structure **70** is formed in accordance with a back end of line (BEOL) scheme adopted for the integrated circuit design. In the BEOL scheme illustrated in FIG. 1, various interconnect levels **100A-100N** have similar features. Other embodiments may utilize alternate integration schemes wherein the various interconnect levels **100A-100N** use different features. For example, the contacts **66**, which are shown as vertical connectors, may be extended to form conductive lines which transport current laterally. As will be subsequently described, the interconnect levels **100A-100N** of the interconnect structure **70** are formed by a dual damascene process.

**[0016]** The interconnect levels **100A-100N** of the interconnect structure **70** each comprise conductive vias and/or conductive lines embedded in an intermetal dielectric (IMD) layer. Generally, vias conduct current vertically and are used to electrically connect two conductive features located at vertically adjacent levels, whereas lines conduct current laterally and are used to distribute electrical signals and power within one interconnect level. In the bottom interconnect level **100A**, conductive vias **104A** connect contacts **66** to conductive lines **108A** and, at subsequent interconnect levels **100B-100N**, vias connect lines on a level below the vias to lines above the vias (e.g., a pair of conductive lines **108A** and **108B** are connected by a conductive via **104B**). In some embodiments, the structures of the various interconnect levels (e.g., the bottom interconnect level **100A** and the subsequent interconnect levels **100B-100N**) may be similar. In the example illustrated in FIG. 1, each of the interconnect levels **100A-100N** comprises conductive vias **104A-104N** and conductive lines **108A-108N** embedded in an IMD **110A-110N** having a planar top surface. Other embodiments may adopt a different scheme. For example, conductive vias **104A** may be omitted from the bottom interconnect level **100A** and the contacts **66** may be directly connected to the conductive lines **108A**.

**[0017]** FIGS. 2 through 10 illustrate cross-sectional views of a semiconductor device at various intermediate stages of fabrication, in accordance with some embodiments. Specifically, the formation of an interconnect level for an interconnect structure is illustrated. FIGS. 2 through 10 are detailed cross-sectional views of a region **101** of FIG. 1, showing a

process for forming an intermediate interconnect level **100N-1** of an interconnect structure **70**. However, any interconnect level of the interconnect structure may be formed using the process. For example, such a process may also be used to form the bottom interconnect level **100A** (see FIG. 1) and/or the top interconnect level **100N** (see FIG. 1) of the interconnect structure.

**[0018]** FIG. 2 illustrates the formation of an etch stop layer (ESL) **202** and a dielectric layer **206**. The ESL **202** and the dielectric layer **206** are formed over a dielectric layer **114** and conductive features **112**. The dielectric layer **114** may be the IMD of an underlying interconnect level (e.g., the IMD **110B** in FIG. 1) or may be an underlying ILD (e.g., the ILD(s) **64** in FIG. 1). The conductive features **112** may be a conductive line of an underlying interconnect level (e.g., the conductive lines **108B** in FIG. 1) or may be an electrically conductive feature in an underlying ILD (e.g., the contacts **66** in FIG. 1).

**[0019]** In some embodiments, the ESL **202** is used for controlling subsequent etching processes to form a via opening (see below, FIG. 8). The ESL **202** may be any acceptable ESL, such as a single-layer ESL, a bi-layer ESL, a tri-layer ESL, or the like. In some embodiments, the ESL **202** is a tri-layer ESL comprising a bottom ESL **202A**, a middle ESL **202B** on the bottom ESL **202A**, and a top ESL **202C** on the middle ESL **202B**. The ESL **202A** comprises an insulating material, such as  $\text{AlO}_x$ ,  $\text{AlN}$ ,  $\text{Al}_2\text{O}_3$ ,  $\text{ZrO}_x$ ,  $\text{YO}_x$ , combinations thereof, or the like, having an etch rate different than an etch rate of the underlying dielectric layer **114** and the subsequently formed overlying material. The ESL **202A** may be formed using PECVD, ALD, CVD, or the like. The ESL **202B** comprises an insulating material, such as  $\text{SiO}$ ,  $\text{SiOC}$ ,  $\text{SiCN}$ ,  $\text{SiON}$ ,  $\text{SiN}$ , or the like. The ESL **202C** may be formed of similar materials and by similar methods as described above for the ESL **202A**. The ESL **202C** may have an etch rate different than an etch rate of the underlying ESL **202B** and the subsequently formed overlying material.

**[0020]** The dielectric layer **206** is formed on the ESL **202**. The dielectric layer **206** is used to form the bulk of an intermetal dielectric (IMD) surrounding conductive vias and conductive lines of the interconnect level **100N-1** (see below, FIG. 10). In some embodiments, the dielectric layer **206** is formed of a porous or dense low dielectric constant (low-k) dielectric such as, e.g., silicon oxycarbide ( $\text{SiOCH}$ ), fluorosilicate glass (FSG), carbon-doped oxide (CDO), a flowable oxide, porous oxides (e.g., xerogels/aerogels), phosphosilicate glass (PSG), borosilicate glass (BSG), boron-doped phosphosilicate glass (BPSG), undoped silicate glass (USG), the like, or a combination thereof. The dielectric layer **206** may also be referred to as a low-k dielectric layer. The dielectric material of the dielectric layer **206** may be deposited using any suitable method, such as CVD, PECVD, FCVD, spin-on coating, the like, or a combination thereof.

**[0021]** In FIG. 3, mask layers **210**, **220**, **230**, and **240** are formed over the dielectric layer **206**. The mask layers **210**, **220**, **230**, and **240** are used to control subsequent etching processes to form openings and trenches for conductive vias and conductive lines, respectively (see below, FIGS. 7-8).

**[0022]** In some embodiments, the mask layer **210** is formed of a dielectric material such as silicon oxide, which may be formed, for example, using tetraethylorthosilicate (TEOS) as a precursor. The dielectric material of the mask layer **210** has a high etching selectivity from the etching of

the mask layers **220** and **230** (described below). In some embodiments, the dielectric material of the mask layer **210** is a metal-free dielectric material. The formation methods of the material of the mask layer **210** may include Chemical Vapor Deposition (CVD), Plasma Enhance Chemical Vapor Deposition (PECVD), Sub Atmosphere Chemical Vapor Deposition (SACVD), or the like.

[0023] Next, the mask layer **220** is formed over the mask layer **210**. The mask layer **220** is formed of a tungsten-containing mask material, such as tungsten carbide, which has a strong physical modulus for subsequent trench patterning (see below, FIGS. 5-8). In some embodiments, the tungsten-containing mask material has a Young's modulus in a range of 500 MPa to 2000 MPa. Because the tungsten-containing mask material has a strong physical modulus, the line width roughness (LWR) of the subsequently patterned trenches may be reduced. Additionally, byproducts of etching the tungsten-containing mask material during the trench patterning process may be volatile (e.g., gas phase instead of solid phase), so that the byproducts may be easily removed from the patterned trenches, which can reduce under-etching (see below, FIGS. 7-8). The material of the mask layer **220** may be formed using PECVD, Atomic Layer Deposition (ALD), CVD, Physical Vapor Deposition (PVD), or the like. The mask layer **220** may be formed to a first thickness  $T_1$  in a range of 30 Å to 200 Å, which may be advantageous for providing a strong physical modulus for line patterning and reduce LWR of subsequently formed trenches in the dielectric layer **206**. Forming the mask layer **220** to a thickness less than 30 Å may lead to increased LWR of subsequently formed conductive lines.

[0024] Next, the mask layer **230** is formed over the mask layer **220**. The mask layer **230** is formed of a titanium-containing mask material, such as titanium nitride, which has a high etching selectivity from the etching of the mask layer **210** and the dielectric layer **206**. In some embodiments, the titanium-containing mask material of the mask layer **230** has a greater etching selectivity from the etching of the mask layer **210** and the dielectric layer **206** than the tungsten-containing mask material of the mask layer **220**. As such, the over-layer window for subsequently forming via openings and trenches in the dielectric layer **206** (see below, FIGS. 5-8) may be improved. The material of the mask layer **230** may be formed using PECVD, Atomic Layer Deposition (ALD), CVD, Physical Vapor Deposition (PVD), or the like. The mask layer **230** may be formed to a second thickness  $T_2$  in a range of 20 Å to 100 Å, which may be advantageous for improving etching selectivity for subsequent etching processes. Forming the mask layer **230** to a thickness less than 20 Å may lead to poorer etching selectivity for subsequent etching processes.

[0025] Next, the mask layer **240** is formed over the mask layer **230**. In some embodiments, the mask layer **220** is formed of a dielectric material such as silicon oxide, which has a high etching selectivity from the etching of the mask layers **220** and **230**. The mask layer **240** may be formed of similar materials and by similar methods as described above for the mask layer **220**.

[0026] In FIG. 4, a photosensitive mask **250** is formed over the mask layer **240**. The photosensitive mask **250** may be any acceptable photoresist, such as a single-layer photoresist, a bi-layer photoresist, a tri-layer photoresist, or the like. In the illustrated embodiment, the photosensitive mask **250** is a tri-layer photoresist including a bottom layer **250A**,

a middle layer **250B**, and a top layer **250C**. In some embodiments, the bottom layer **250A** is formed of amorphous carbon, the middle layer **250B** is formed of a silicon-containing photoresist or film, and the top layer **250C** is formed of a photosensitive material. The top layer **250C** is patterned with openings having first widths  $W_1$  in a range of 5 nm to 40 nm, which are suitable for subsequently patterning trenches for conductive lines (see below, FIGS. 8-9) in the dielectric layer **206**.

[0027] In FIG. 5, the photosensitive mask **250** is used as an etching mask to etch and pattern the mask layers **240**, **230**, and **220**, thus forming masks having openings **242** that will be used in subsequent etching processes to form trenches for conductive lines in the dielectric layer **206**. The openings **242** are formed through the mask layers **240**, **230**, and **220**. In some embodiments, the openings **242** extend into (but not through) the mask layers **210**. One or more layers of the photosensitive mask **250** may be consumed in the etching process, or may be removed after the etching process. In some embodiments, the photosensitive mask **250** is removed by an ashing process followed by a wet clean process. After the etching process and the removal of the photosensitive mask **250**, remaining portions of the patterned mask layer **240** can have a reduced thickness. Alternatively, the thickness of the patterned mask layer **240** may be substantially unchanged by the etching process.

[0028] The etching may be any acceptable etch process, such as a reactive ion etch (RIE), neutral beam etch (NBE), the like, or a combination thereof. In some embodiments, the etch process is an anisotropic dry etch performed by a plasma process. The plasma etching process is performed in a processing chamber with process gas(es) being supplied into the processing chamber. In some embodiments, the plasma is a direct plasma. In some embodiments, the plasma is a remote plasma that is generated in a separate plasma generation chamber connected to the processing chamber. Process gas(es) can be activated into plasma by any suitable method of generating the plasma, such as transformer coupled plasma (TCP) systems, inductively coupled plasma (ICP) systems, capacitively coupled plasma (CCP) systems, magnetically enhanced reactive ion techniques, electron cyclotron resonance techniques, or the like.

[0029] The process gas(es) used in the plasma etching process include one or more etchant gas(es). In some embodiments, the etchant gas(es) are chlorine-based etchant gas(es) such as  $\text{Cl}_2$ ,  $\text{BCl}_3$ , the like, or combinations thereof. Additional process gas(es) such as oxygen gas and/or hydrogen gas may also be used. Carrier gas(es), such as  $\text{N}_2$ , Ar, He, or the like, may be used to carry the process gas(es) into the processing chamber. The process gas(es) may be flowed into the processing chamber at a rate in a range of 100 sccm to 1000 sccm.

[0030] The plasma etching process may be performed using a bias voltage in a range of 50 volts to 500 volts. The plasma etching process may be performed using a plasma generation power in a range of 0 watts to 500 watts. The plasma etching process may be performed at a temperature in a range of 20° C. to 60° C. A pressure in the processing chamber may be in a range of 20 mTorr to 80 mTorr. The plasma etching process can be performed for a duration in a range of 50 seconds to 200 seconds. Performing the plasma etching process with etching parameters (e.g., bias voltage,

duration, etc.) outside of the ranges discussed herein may cause undesirable under-etching or over-etching of the mask layers **210**.

**[0031]** In FIG. 6, a photosensitive mask **260** is formed over the mask layer **240** and fills the openings **242**. The photosensitive mask **260** may be any acceptable photoresist, such as a single-layer photoresist, a bi-layer photoresist, a tri-layer photoresist, or the like. In the illustrated embodiment, the photosensitive mask **260** is a tri-layer photoresist including a bottom layer **260A**, a middle layer **260B**, and a top layer **260C**. In some embodiments, the photosensitive mask **260** is formed of similar materials and by similar methods as described above for the photosensitive mask **250** (see above, FIG. 4). The top layer **260C** is patterned with openings having second widths  $W_2$  in a range of 5 nm to 30 nm, which are suitable for subsequently patterning openings for conductive vias (see below, FIGS. 8-9) in the dielectric layer **206**. The second widths  $W_2$  are smaller than the first widths  $W_1$  of the openings in the photosensitive mask **250** (see above, FIG. 4).

**[0032]** In FIG. 7, a patterning process is performed to transfer the pattern of the photosensitive mask **260** to the mask layer **210** and the dielectric layer **206**. The patterning process forms via openings **204** through the mask layer **210** and extending into dielectric layer **206**. In some embodiments, the patterning process may comprise one or more etching processes, where the photosensitive mask **260** is used as an etch mask. The one or more etching processes may include suitable anisotropic dry etching processes, such as a reactive ion etching (RIE) process, or the like. In some embodiments, the etch process is an anisotropic dry etch performed by a plasma process, such as the plasma etching process described above with respect to FIG. 5. In another embodiment, an etchant mixture for the etch process may comprise fluorine-based etchants, such as  $C_xF_y$ , (e.g.,  $CF_4$ ,  $C_4F_8$ , etc.),  $NF_3$ , the like, or combinations thereof, similar to the plasma etching process that will be described below with respect to FIG. 8. In some embodiments, the via openings **204** in the mask layer **210** and the dielectric layer **206** may have approximately the same width  $W_2$  (see above, FIG. 6) as the openings in the photosensitive mask **260**. Timed etching processes may be used to etch the dielectric layer **206** until the via openings **204** extend partially into the dielectric layer **206** by a desired distance. After forming the via openings **204** in the mask layer **210** and the dielectric layer **206**, the photosensitive mask **260** (see above, FIG. 6) may be removed with a suitable process, such as an ashing process followed by a wet clean process.

**[0033]** In FIG. 8, a patterning process is performed to transfer the pattern of the openings in the mask layers **220**, **230**, and **240** to the dielectric layer **206**, thereby forming trenches **208** in the mask layer **210** and the dielectric layer **206**, and extending the via openings **204** through the dielectric layer **206**. After they are extended through the dielectric layer **206**, the via openings **204** extend from the bottoms of the trenches **208** to the ESL **202**. The via openings **204** and trenches **208** will be subsequently filled to form conductive vias and conductive lines, respectively (see below, FIGS. 9-10). As will be subsequently described in greater detail, the patterning process may comprise one or more etching processes, where the mask layers **220**, **230**, and **240** (see above, FIG. 7) are used as an etch mask, and portions of the mask layer **210** not covered by the mask layers **220**, **230**, and **240** are removed by the one or more etching processes so

that the trenches **208** extend into the dielectric layer **206** and the via openings **204** extend through the dielectric layer **206**. The etchant may be chosen to be selective to the material of the mask layers **210** and **240** and the dielectric layer **206**, with little or no etching of the mask layers **220** and **230**. In some embodiments, the mask layer **240** is removed by the one or more etching processes. For example, when the mask layers **210** and **240** are formed of the same material (e.g., silicon oxide), the mask layer **240** may be removed by the etching process used to form the trenches **208** in the mask layer **210** and the dielectric layer **206**. The via openings **204** may then be extended through the ESL **202** by acceptable etching techniques to expose the top surfaces of the conductive features **112**. In some embodiments, the trenches **208** have third widths  $W_3$  in a range of 5 nm to 40 nm, and the via openings **204** have fourth widths  $W_4$  in a range of 5 nm to 30 nm.

**[0034]** In some embodiments, the patterning process for the dielectric layer **206** may comprise one or more etching processes, where the mask layers **220**, **230**, and **240** are used as an etch mask. The etching may be any acceptable etch process, such as a reactive ion etch (RIE), neutral beam etch (NBE), the like, or a combination thereof. In some embodiments, the etch process is an anisotropic dry etch performed by a plasma process. The plasma etching process is performed in a processing chamber with process gas(es) being supplied into the processing chamber. In some embodiments, the plasma is a direct plasma. In some embodiments, the plasma is a remote plasma that is generated in a separate plasma generation chamber connected to the processing chamber. Process gas(es) can be activated into plasma by any suitable method of generating the plasma, such as transformer coupled plasma (TCP) systems, inductively coupled plasma (ICP) systems, capacitively coupled plasma (CCP) systems, magnetically enhanced reactive ion techniques, electron cyclotron resonance techniques, or the like.

**[0035]** The process gas(es) used in the plasma etching process include one or more etchant gas(es). In some embodiments, the etchant gas(es) are fluorine-based etchant gas(es) such as  $C_xF_y$ , (e.g.,  $CF_4$ ,  $C_4F_8$ , etc.),  $NF_3$ , the like, or combinations thereof. Additional process gas(es) such as oxygen gas, hydrogen gas, and/or  $C_xO_y$  gas, may also be used. Carrier gas(es), such as  $N_2$ , Ar, He, or the like, may be used to carry the process gas(es) into the processing chamber. The process gas(es) may be flowed into the processing chamber at a rate in a range of 100 sccm to 1000 sccm.

**[0036]** The plasma etching process may be performed using a bias voltage in a range of 30 volts to 1000 volts. The plasma etching process may be performed using a plasma generation power in a range of 30 watts to 1000 watts. The plasma etching process may be performed at a temperature in a range of 20° C. to 60° C. A pressure in the processing chamber may be in a range of 3 mTorr to 80 mTorr. The plasma etching process can be performed for a duration in a range of 30 seconds to 200 seconds. Performing the plasma etching process with etching parameters (e.g., bias voltage, duration, etc.) outside of the ranges discussed herein may cause an undesirable under-etching or over-etching of the dielectric layer **206**.

**[0037]** As noted above, the mask layer **220** is formed of a tungsten-containing mask material and the mask layer **230** is formed of a titanium-containing mask material. In some embodiments in which fluorine-based etchant gas(es) are used to transfer the pattern of the photosensitive mask **260**



to the mask layer **210** and the dielectric layer **206**, the etchant gas(es) may react with the titanium-containing mask material to form titanium-containing byproducts such as  $\text{TiF}_4$ , and the etchant gas(es) may react with the tungsten-containing mask material to form tungsten-containing byproducts such as  $\text{WF}_6$ . For example, when the mask layer **220** is formed of tungsten carbide (WC) and the etchant gas(es) include oxygen ( $\text{O}_2$ ) and nitrogen trifluoride ( $\text{NF}_3$ ), byproducts such as tungsten hexafluoride ( $\text{WF}_6$ ), carbon monoxide (CO), and carbon fluoride ( $\text{C}_x\text{F}_y$ ) may be formed according to:  $\text{WC} + \text{O}_2 + \text{NF}_3 \rightarrow \text{WF}_6 + \text{CO} + \text{C}_x\text{F}_y$ . Remaining byproducts on the sidewalls or bottom surfaces of the openings **242** and **204** may lead to under-etching of subsequently formed trenches and openings for conductive lines and conductive vias, which can cause increased contact resistance and degradation of device performance. Because  $\text{TiF}_4$  has a boiling point of about  $284^\circ\text{C}$ ., it may be difficult to remove from the sidewalls or bottom surfaces of the openings **242** and **204**. Advantageously,  $\text{WF}_6$  has a boiling point of about  $17^\circ\text{C}$ ., so it may be easily removed from the sidewalls or bottom surfaces of the openings **242** and **204** by, e.g., sublimation or evaporation at room temperature (e.g., about  $25^\circ\text{C}$ .). In some embodiments, the plasma etching process is performed at a temperature that is above the boiling point of  $\text{WF}_6$  and below the boiling point of  $\text{TiF}_4$ , such as at about room temperature of about  $25^\circ\text{C}$ .

**[0038]** Using the mask layer **220** in combination with the mask layer **230** allows for a reduction in titanium-containing byproducts, as compared to using a thicker mask layer **230** without the mask layer **220**. Further, using the mask layer **230** in combination with the mask layer **220** retains the advantages of a titanium-containing mask material, such as improving etching selectivity from the etching of the mask layer **210** and the dielectric layer **206**, as compared to using a thicker mask layer **220** without the mask layer **230**.

**[0039]** In FIG. 9, a conductive material **290** is formed over the structure to fill (or overfill) the via openings **204** and the trenches **208** (see above, FIG. 8). In some embodiments, the conductive material **290** includes a conductive diffusion barrier liner lining the sidewalls and bottom surfaces of the via openings **204** and the trenches **208**, and a conductive fill material over the conductive diffusion barrier liner. The conductive diffusion barrier liner may reduce out-diffusion of conductive materials into the dielectric layer **206**. The conductive diffusion barrier line may comprise one or more layers of TaN, Ta, TiN, Ti, Co, the like, or combinations thereof. The conductive diffusion barrier liner may be deposited by any suitable method, such as CVD, PECVD, PVD, ALD, PEALD, electrochemical plating (ECP), electroless plating and the like. The conductive fill material may comprise metals such as Cu, W, Co, Ru, CuMn, Mo, Al, or the like, or combinations thereof, or multi-layers thereof. The conductive fill material may be deposited by any suitable method, for example, CVD, PECVD, PVD, ALD, PEALD, electrochemical plating (ECP), electroless plating and the like. In some embodiments, a thin conductive seed layer may be deposited over the conductive diffusion barrier liner to help initiate an ECP process in which the conductive fill material fills the openings. In some embodiments, the conductive seed layer may be of the same conductive material as the conductive fill material and may be deposited using a suitable deposition technique (e.g., CVD, PECVD, ALD, PEALD, or PVD, or the like).

**[0040]** In FIG. 10, a removal process is performed to remove excess portions of the conductive material **290**, which excess portions are over the top surface of the dielectric layer **206**. The removal process also removes the remaining portions of the mask layers **210**, **220**, and **230** (see above, FIG. 9) over the dielectric layer **206**. After the removal process, the conductive material **290** has portions remaining in the via openings **204** (thus forming conductive vias **104N-1**) and has portions remaining in the trenches **208** (thus forming conductive lines **108N-1**). The remaining portions of the dielectric layer **206** are an IMD **110N-1** that is disposed around the conductive vias **104N-1** and the conductive lines **108N-1**. The removal process may be a planarizing process such as a CMP or the like. After the planarizing process, top surfaces of the conductive lines **108N-1** and the IMD **110N-1** are coplanar (within process variations). The removal process completes fabrication of the interconnect level **100N-1**, which comprises conductive vias **104N-1** and conductive lines **108N-1** embedded in IMD **110N-1**.

**[0041]** Additional interconnect levels may be formed after the process described for FIGS. 2-10. FIG. 11 illustrates an interconnect level **100N** which is formed on the intermediate interconnect level **100N-1**. The interconnect level **100N** comprises a conductive via **104N** and a conductive line **108N** in an IMD **110N**. The IMD **110N** is formed from, e.g., a dielectric layer **306**. The interconnect level **100N** may be formed of similar materials and by similar methods as described above for the interconnect level **100N-1** (see above, FIGS. 2-10).

**[0042]** Embodiments may achieve advantages. Multi-layer masks including a titanium-containing mask layer over a tungsten-containing mask layer are formed for the patterning of interconnect openings (including trenches and via openings) with a dual damascene process. The titanium-containing mask layer may have improved etching selectivity with underlying dielectric materials for patterning the interconnect openings. The tungsten-containing mask layer may have a strong physical modulus, which may reduce the line width roughness (LWR) of subsequently formed conductive lines. Further, inclusion of the tungsten-containing mask layer in the multi-layer mask helps reduce the quantity of non-volatile etching byproducts during the patterning of the interconnect openings, thereby reducing under-etching.

**[0043]** In accordance with an embodiment, a method includes: depositing a first dielectric layer over a first conductive feature; depositing a first mask layer over the first dielectric layer, the first mask layer including tungsten carbide; depositing a second mask layer over the first mask layer, the second mask layer including titanium nitride; patterning a first opening in the first mask layer and the second mask layer, the first opening having a first width; patterning a second opening in a bottom surface of the first opening, the second opening extending into the first dielectric layer, the second opening having a second width, the second width being less than the first width; and extending the first opening into the first dielectric layer and extending the second opening through the first dielectric layer to expose a top surface of the first conductive feature. In an embodiment, the first mask layer has a first thickness in a range of  $30\text{ \AA}$  to  $200\text{ \AA}$ . In an embodiment, the second mask layer has a second thickness in a range of  $20\text{ \AA}$  to  $100\text{ \AA}$ . In an embodiment, the method further includes filling the first opening and the second opening with a conductive material.

In an embodiment, filling the first opening forms a conductive line in the first opening, the conductive line having a third width in a range of 5 nm to 40 nm. In an embodiment, filling the second opening forms a conductive via in the second opening, the conductive via having a fourth width in a range of 5 nm to 30 nm. In an embodiment, the method further includes forming a third mask layer over the second mask layer. In an embodiment, the third mask layer includes silicon oxide.

**[0044]** In accordance with another embodiment, a method includes: depositing a first mask layer over a low-k dielectric layer, the first mask layer being silicon oxide; depositing a second mask layer over the first mask layer, the second mask layer being tungsten carbide; depositing a third mask layer over the second mask layer, the third mask layer being titanium nitride; depositing a fourth mask layer over the third mask layer, the fourth mask layer being silicon oxide; patterning the second mask layer, the third mask layer, and the fourth mask layer to form a trench; extending the trench into the low-k dielectric layer by etching through the first mask layer; forming a conductive line by filling the trench with a conductive material; and removing the first mask layer, the second mask layer, the third mask layer, and the fourth mask layer. In an embodiment, etching through the first mask layer includes etching the first mask layer with a fluorine-based etchant. In an embodiment, the second mask layer has a Young's modulus in a range of 500 MPa to 2000 MPa. In an embodiment, removing the fourth mask layer is performed while etching through the first mask layer. In an embodiment, forming the conductive line includes planarizing the conductive material, and wherein the first mask layer, the second mask layer, and the third mask layer are removed by the planarizing of the conductive material.

**[0045]** In accordance with yet another embodiment, a method includes: forming a first mask layer over a first dielectric layer, the first dielectric layer being over a first conductive feature, the first mask layer including tungsten carbide; forming a second mask layer over the first mask layer, the second mask layer including titanium nitride; patterning the first mask layer and the second mask layer; and after patterning the first mask layer and the second mask layer, forming an opening extending into the first dielectric layer by etching the first dielectric layer with a fluorine-based etchant using the first mask layer and the second mask layer as an etching mask, the opening exposing a top surface of the first conductive feature, the etching the first dielectric layer with the fluorine-based etchant being performed at a first temperature, wherein a first byproduct of the fluorine-based etchant with the first mask layer has a boiling point less than the first temperature. In an embodiment, a second byproduct of the fluorine-based etchant with the second mask layer has a boiling point greater than the first temperature. In an embodiment, the second byproduct is  $\text{TiF}_4$ . In an embodiment, the first byproduct is  $\text{WF}_6$ . In an embodiment, the etching the first dielectric layer is performed with a plasma etching process, and the fluorine-based etchant is  $\text{CF}_4$ . In an embodiment, the plasma etching process is performed at a temperature in a range of 20° C. to 60° C. In an embodiment, the first temperature is room temperature.

**[0046]** In accordance with an embodiment, a method comprising: forming an intermediate dielectric layer over a conductive feature, wherein the forming the intermediate dielectric layer comprises: forming an etch stop structure on the top surface of the conductive feature and on a top surface

of a first dielectric layer, wherein the conductive feature is embedded in the first dielectric layer; forming a second dielectric layer on a top surface of the etch stop structure; and forming a silicon oxide layer on a top surface of the second dielectric layer; forming a tungsten carbide layer over the intermediate dielectric layer; forming a titanium nitride layer over the tungsten carbide layer; performing a first etch to form a first opening through the tungsten carbide layer and the titanium nitride layer; and performing a second etch at a first temperature on the intermediate dielectric layer through the first opening to form a second opening, the second opening exposing a top surface of the conductive feature, wherein the second etch utilizes an etchant that reacts with the tungsten carbide layer to form a byproduct with a boiling point less than the first temperature. In an embodiment, the performing the first etch forms the first opening through the silicon oxide layer and into a first portion of the second dielectric layer and wherein the performing the second etch forms the second opening through a remainder of the second dielectric layer and through the etch stop structure to the top surface of the conductive feature. In an embodiment, the forming the etch stop structure comprises: forming a bottom etch stop layer (ESL) on the top surface of the conductive feature; forming a middle ESL on the bottom ESL opposite the conductive feature; and forming a top ESL on the middle ESL opposite the bottom ESL. In an embodiment, the bottom ESL comprises an aluminum-containing compound, the middle ESL comprises a silicon compound, and the top ESL comprises an aluminum alloy. In an embodiment the method further comprises: prior to the performing the first etch, performing a first pattern etch through the titanium nitride layer, through the tungsten carbide layer, and into the intermediate layer to form a first pattern hole; forming a bottom photoresist layer in and over the first pattern hole; forming a middle photoresist layer on the bottom photoresist layer opposite titanium nitride layer; forming a top photoresist layer on the middle photoresist layer opposite the bottom photoresist layer; and performing a second pattern etch through the top photoresist layer to form a second pattern hole. In an embodiment the first pattern hole is formed to a first width, the second pattern hole is formed to a second width smaller than the first width, and wherein the first opening has the first width and wherein the second opening has the second width.

**[0047]** In accordance with another embodiment, a comprising: forming a porous dielectric layer over a conductive line; forming a tungsten carbide mask over the porous dielectric layer; forming a titanium nitride mask over the tungsten carbide mask; etching a first hole through the tungsten carbide mask and through the titanium nitride mask, wherein the first hole has a first width; etching a second hole into the porous dielectric layer, the second hole being formed in a bottom of the first hole, wherein the second hole has a second width, the second width being less than the first width; extending the first hole into the porous dielectric layer, wherein after the extending the first hole the first hole has the first width; and extending the second hole through a remainder of the porous dielectric layer, wherein after the extending the second hole the second hole has the second width, wherein the extending the second hole exposes the conductive line. In an embodiment the extending the first hole and the extending the second hole comprises utilizing etchant gases that react with the tungsten carbide mask to form byproducts which undergo sublima-

tion at room temperature. In an embodiment the method further comprises, after the extending the first hole and the extending the second hole, over filling the first hole and the second hole with a conductive material. In an embodiment after the over filling the first hole and the second hole with the conductive material, performing a removal process to remove the tungsten carbide mask, the titanium nitride mask and excess portions of the conductive material within the tungsten carbide mask and the titanium nitride mask. In an embodiment the removal process forms a planar top surface shared by the conductive material and the porous dielectric layer. In an embodiment the porous dielectric layer comprises aerogel. In an embodiment prior to the forming the porous dielectric layer, forming a tri-layer etch stop layer in physical contact with the conductive line.

**[0048]** The foregoing outlines features of several embodiments so that those skilled in the art may better understand the aspects of the present disclosure. Those skilled in the art should appreciate that they may readily use the present disclosure as a basis for designing or modifying other processes and structures for carrying out the same purposes and/or achieving the same advantages of the embodiments introduced herein. Those skilled in the art should also realize that such equivalent constructions do not depart from the spirit and scope of the present disclosure, and that they may make various changes, substitutions, and alterations herein without departing from the spirit and scope of the present disclosure.

What is claimed is:

1. A method comprising:
  - performing a first etching process to form a first opening in a first mask layer;
  - performing a second etching process to extend the first opening into a low-k dielectric layer;
  - after extending the first opening, filling the first opening with a conductive material; and
  - planarizing the conductive material with the low-k dielectric layer, wherein the planarizing removes the first mask layer, a second mask layer, a third mask layer, and a fourth mask layer.
2. The method of claim 1, wherein the performing the second etching process extends the first opening through an etch stop layer.
3. The method of claim 2, wherein the etch stop layer comprises:
  - a bottom etch stop layer comprising a first material;
  - a middle etch stop layer comprising a second material different from the first material; and
  - a top etch stop layer comprising a third material different from the second material.
4. The method of claim 3, wherein the first material is aluminum oxide.
5. The method of claim 4, wherein the second material is silicon oxide.
6. The method of claim 5, wherein the third material is the same as the first material.

7. The method of claim 1, wherein the second mask layer has a thickness of between about 30 Å and about 200 Å.

8. A method of manufacturing a semiconductor device, the method comprising:

- forming a porous dielectric layer over a conductive line;
- forming a tungsten carbide mask over the porous dielectric layer;

- forming a titanium nitride mask over the tungsten carbide mask;

- forming a first hole extending through the tungsten carbide mask and through the titanium nitride mask, wherein the first hole has a first width; and

- forming a second hole extending through the porous dielectric layer from the first hole, wherein the second hole has a second width, the second width being less than the first width.

9. The method of claim 8, wherein the forming the titanium nitride mask forms the titanium nitride mask to a thickness of between about 20 Å and about 100 Å.

10. The method of claim 8, wherein the forming the tungsten carbide mask forms the tungsten carbide mask to a thickness of between about 30 Å and about 200 Å.

11. The method of claim 8, wherein the first width is between about 5 nm and about 40 nm.

12. The method of claim 11, wherein the second width is between about 5 nm and about 30 nm.

13. The method of claim 8, further comprising depositing a conductive material into the first hole and the second hole.

14. The method of claim 8, further comprising forming a tri-layer etch stop layer on the conductive line prior to the forming the porous dielectric layer.

15. A method of manufacturing a semiconductor device, the method comprising:

- forming a first mask layer over a low-k dielectric layer;
- forming a second mask layer over the first mask layer;

- forming a third mask layer over the second mask layer;

- forming a fourth mask layer over the third mask layer;

- forming a conductive material extending through the first mask layer, the second mask layer the third mask layer, and the fourth mask layer; and

- planarizing the conductive material, wherein the planarizing the conductive material removes the fourth mask layer, the third mask layer, the second mask layer, and the first mask layer.

16. The method of claim 15, wherein the forming the first mask layer comprises forming silicon oxide.

17. The method of claim 16, wherein the forming the second mask layer comprises forming tungsten carbide.

18. The method of claim 17, wherein the forming the third mask layer comprises forming titanium nitride.

19. The method of claim 18, wherein the forming the fourth mask layer comprises forming tungsten carbide.

20. The method of claim 15, further comprising:

- forming a tri-layer etch stop layer; and

- forming the low-k dielectric layer over the tri-layer etch stop layer.

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